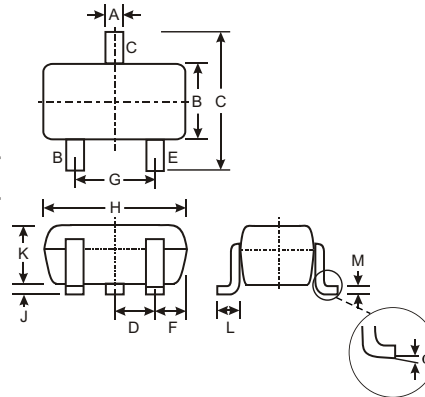


Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDTC)
- Built-In Biasing Resistor, R2 only

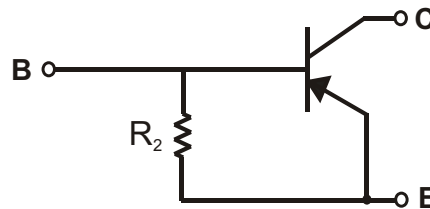
Mechanical Data

- Case: SOT-323, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: Date Code and Marking Code (See Diagrams & Page 2)
- Weight: 0.006 grams (approx.)
- Ordering Information (See Page 2)



SOT-323		
Dim	Min	Max
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
	0	8
All Dimensions in mm		

P/N	R2 (NOM)	MARKING
DDTA114GUA	10K	P26
DDTA124GUA	22K	P27
DDTA144GUA	47K	P28
DDTA115GUA	100K	P29



SCHEMATIC DIAGRAM

Maximum Ratings @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _{C (Max)}	-100	mA
Power Dissipation	P _d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{JA}	625	C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	C

Note: 1. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ T_A = 25 C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	-50			V	I _C = -50 A
Collector-Emitter Breakdown Voltage		BV _{CEO}	-50			V	I _C = -1mA
Emitter-Base Breakdown Voltage		BV _{EBO}	5			V	I _E = -720 A, DDTA114GUA I _E = -330 A, DDTA124GUA I _E = -160 A, DDTA144GUA I _E = -72 A, DDTA115GUA
Collector Cutoff Current		I _{CBO}			-0.5	A	V _{CB} = -50V
Emitter Cutoff Current		I _{EBO}	-300 -140 -65 -30		-580 -260 -130 -58	A	V _{EB} = -4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}			-0.3	V	I _C = -10mA, I _B = -0.5mA
DC Current Transfer Ratio		h _{FE}	30 56 68 82				I _C = -5mA, V _{CE} = -5V
Bleeder Resistor (R ₂) Tolerance		DR ₂	-30		+30	%	
Gain-Bandwidth Product*		f _T		250		MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz

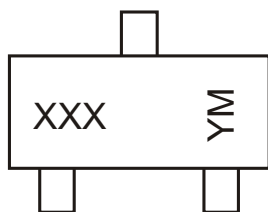
* Transistor - For Reference Only

Ordering Information (Note 2)

Device	Packaging	Shipping
DDTA114GUA-7	SOT-323	3000/Tape & Reel
DDTA124GUA-7	SOT-323	3000/Tape & Reel
DDTA144GUA-7	SOT-323	3000/Tape & Reel
DDTA115GUA-7	SOT-323	3000/Tape & Reel

Notes: 2. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



XXX = Product Type Marking Code
See Sheet 1 Diagrams
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

TYPICAL CURVES - DDTA114GUA

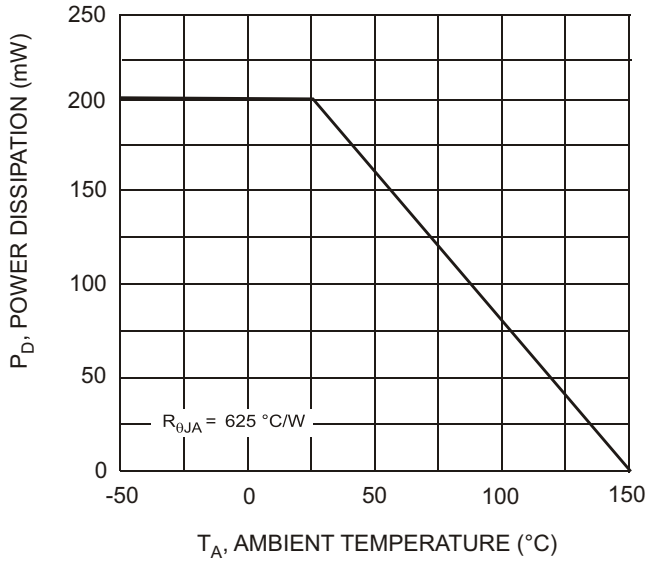


Fig. 1, Derating Curve

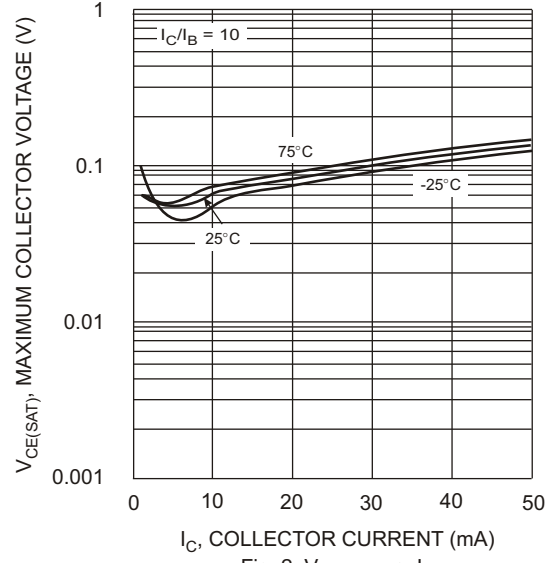


Fig. 2 $V_{CE(SAT)}$ vs. I_C

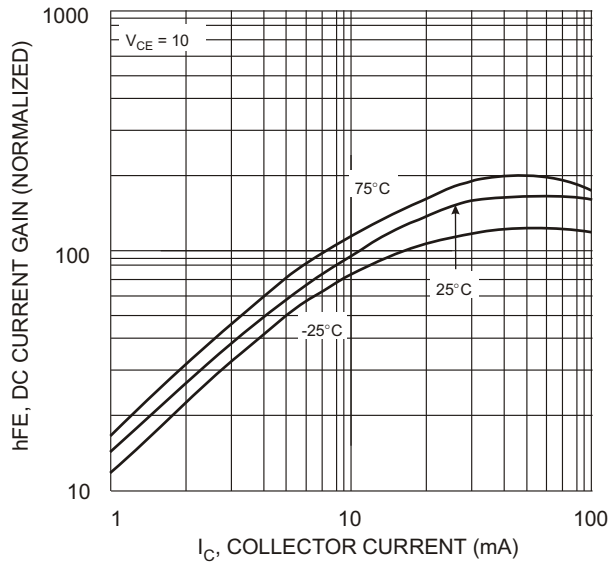


Fig. 3 DC CURRENT GAIN

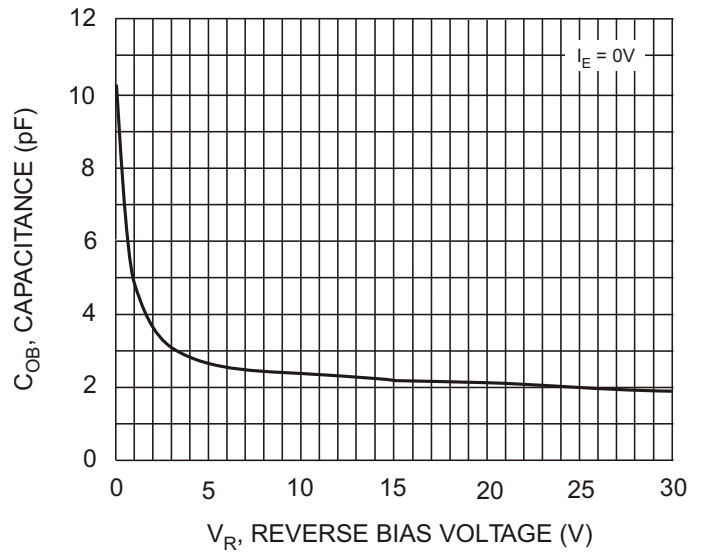


Fig. 4 Output Capacitance

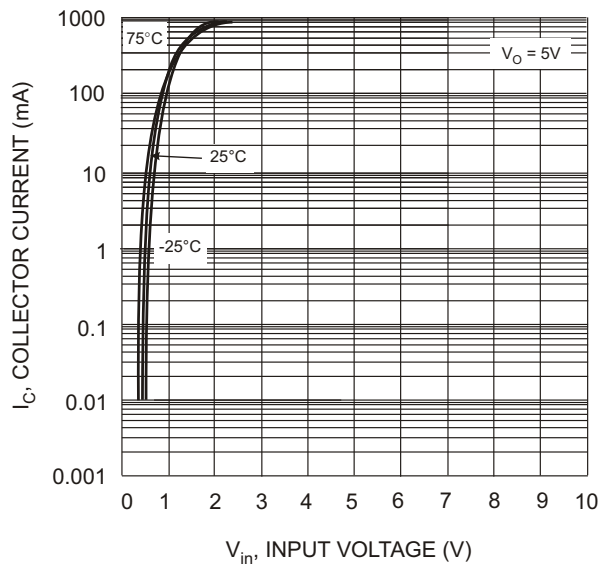


Fig. 5 Collector Current Vs. Input Voltage

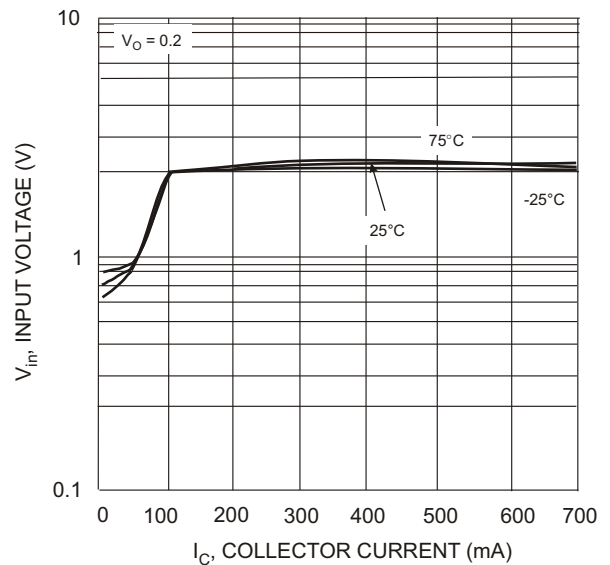


Fig. 6 Input Voltage vs. Collector Current